

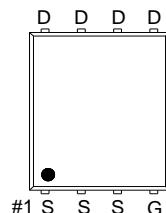
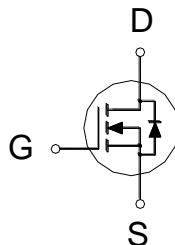
NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PF2115AK**

PDFN 5x6P

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
150V	21mΩ	38A

**ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	38	A
	$T_C = 100^\circ\text{C}$		24	
Pulsed Drain Current ¹		I_{DM}	136	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	6.8	W
	$T_A = 70^\circ\text{C}$		5.4	
Avalanche Current		I_{AS}	15.7	
Avalanche Energy	$L = 1\text{mH}$	E_{AS}	123	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	69	W
	$T_C = 100^\circ\text{C}$		27	
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2.2	W
	$T_A = 70^\circ\text{C}$		1.4	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10\text{s}$	$R_{\theta JA}$		56	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		78	
Junction-to-Case		$R_{\theta JC}$		1.8	

¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	150			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2	3	4	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 150\text{V}, V_{\text{GS}} = 0\text{V}$			1	
		$V_{\text{DS}} = 150\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 55^\circ\text{C}$			10	μA
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		16.7	21	$\text{m}\Omega$
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_D = 20\text{A}$		55		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 75\text{V}, f = 1\text{MHz}$		1980		
Output Capacitance	C_{oss}			149		pF
Reverse Transfer Capacitance	C_{rss}			8.8		
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$		2		Ω
Total Gate Charge ²	Q_g	$V_{\text{DS}} = 75\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		28		
Gate-Source Charge ²	Q_{gs}			8.7		nC
Gate-Drain Charge ²	Q_{gd}			6		
Turn-On Delay Time ²	$t_{d(\text{on})}$	$V_{\text{DS}} = 75\text{V}, I_D \approx 20\text{A}, V_{\text{GS}} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		15		
Rise Time ²	t_r			62		nS
Turn-Off Delay Time ²	$t_{d(\text{off})}$			29		
Fall Time ²	t_f			67		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current	I_S				38	A
Forward Voltage ¹	V_{SD}	$I_F = 20\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		63		nS
Reverse Recovery Charge	Q_{rr}			107		nC

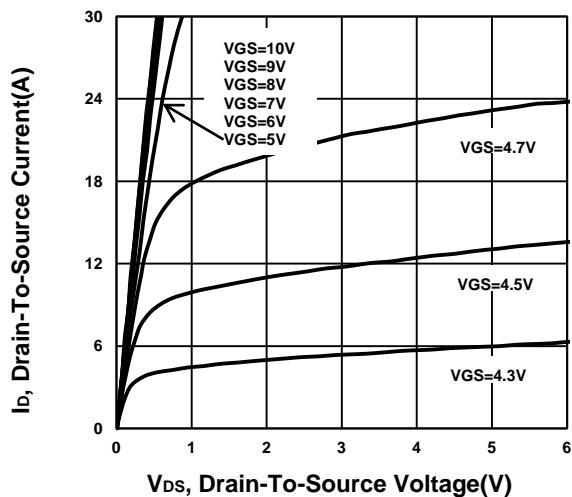
¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.

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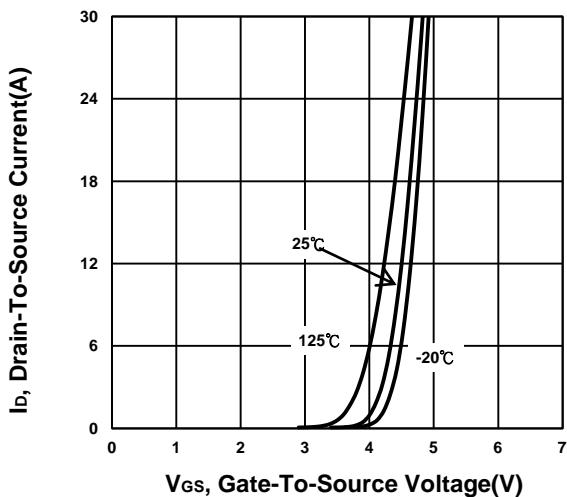
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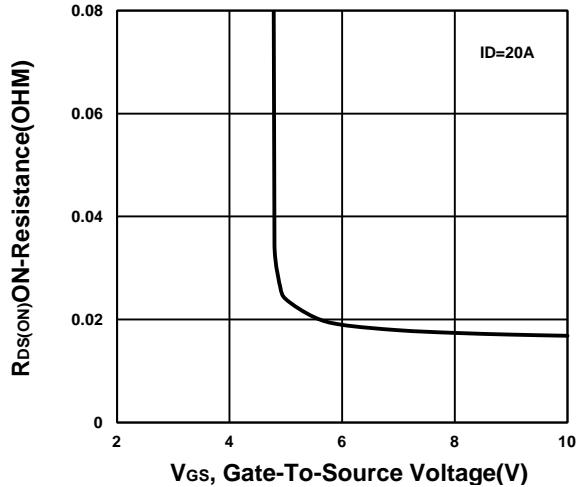
Output Characteristics



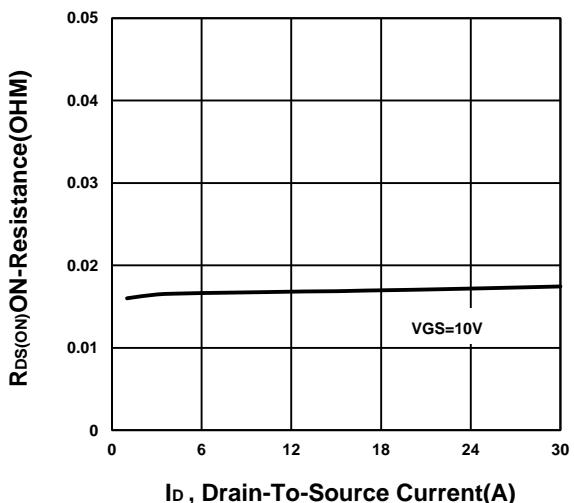
Transfer Characteristics



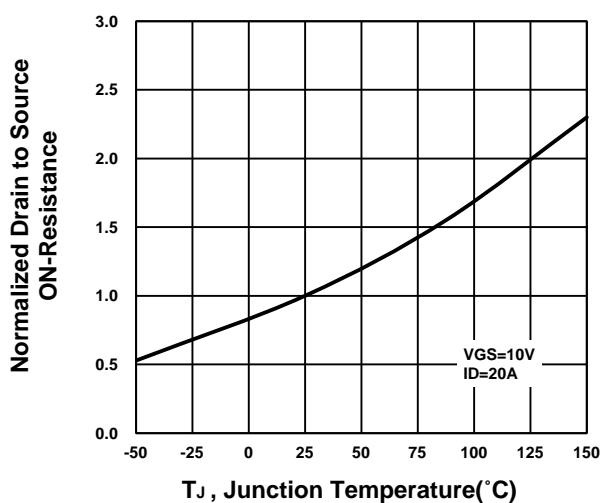
On-Resistance VS Gate-To-Source Voltage



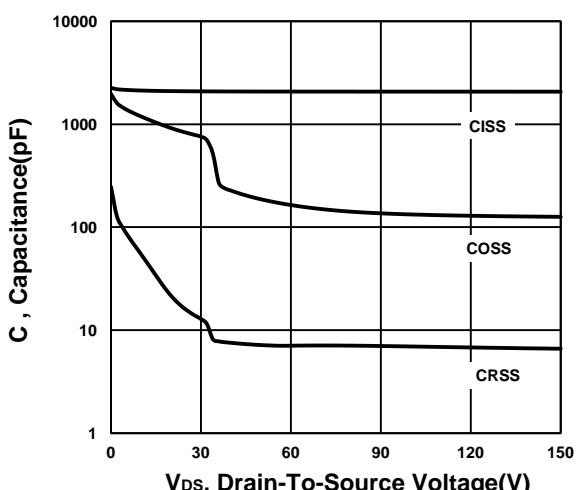
On-Resistance VS Drain Current



On-Resistance VS Temperature



Capacitance Characteristic

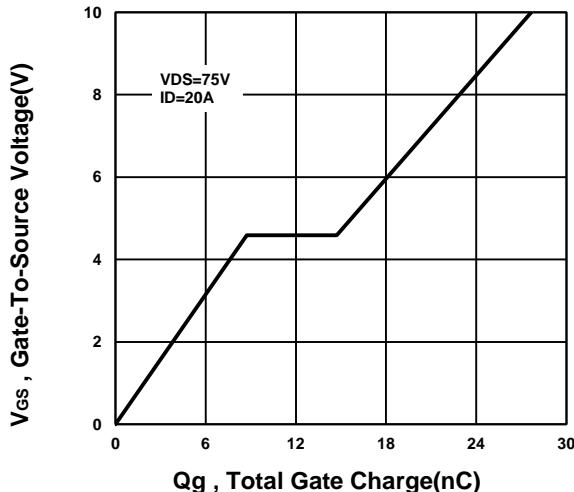


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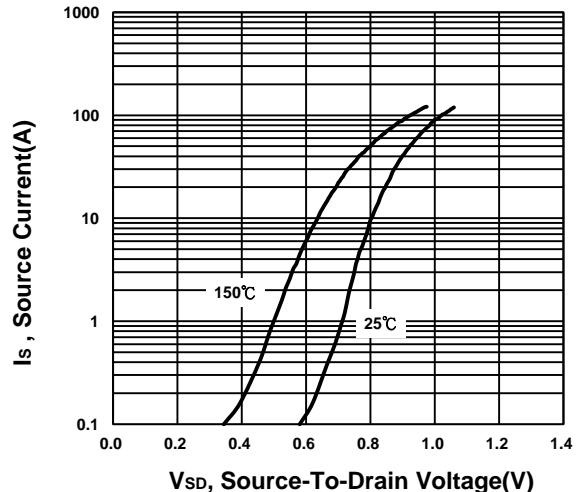
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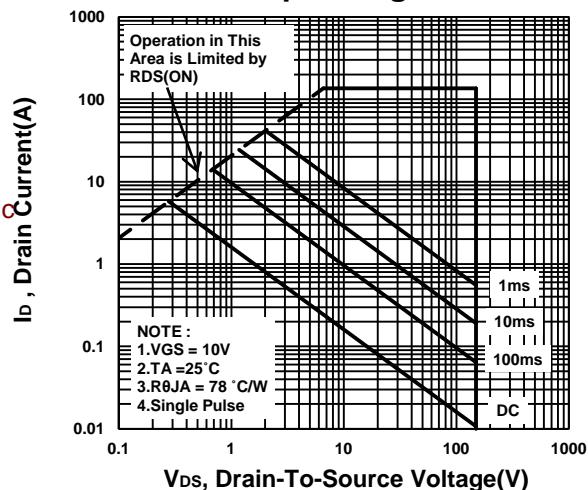
Gate charge Characteristics



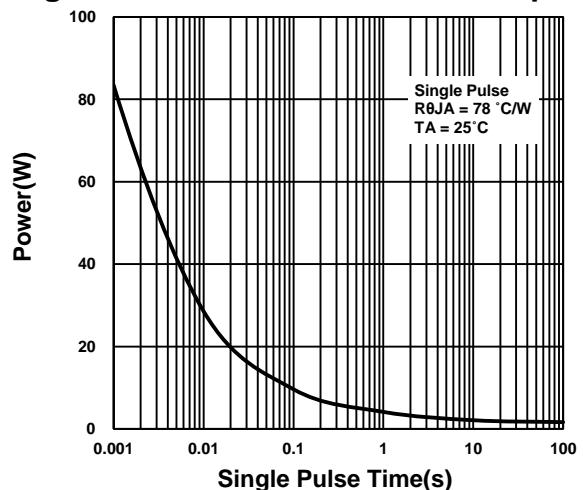
Source-Drain Diode Forward Voltage



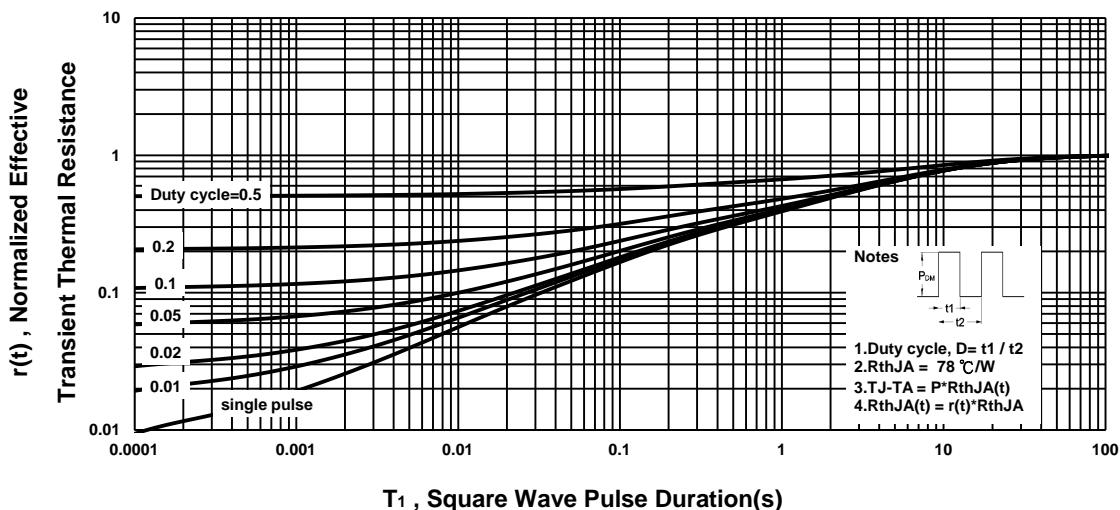
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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